



## Description

SP0080TALC thyristor is a type of protection semiconductor component. It is designed to protect baseband equipment from damaging overvoltage transients, such as modems, telephones, line cards, answering machines, FAX machines, T1/E1, xDSL and more.

## Features

- Lower capacitance
- Low profile package
- Low on-state voltage
- Excellent capability of absorbing transient surge
- Quick response to surge voltage (ns Level)
- Eliminates overvoltage caused by fast rising transients
- Moisture sensitivity level: Level 1
- Non degenerative
- Flammability Rating: UL 94 V-0
- Halogen free and RoHS compliant

## Schematic Symbol



## Limiting Values

(T<sub>A</sub> = 25 °C, unless otherwise specified)

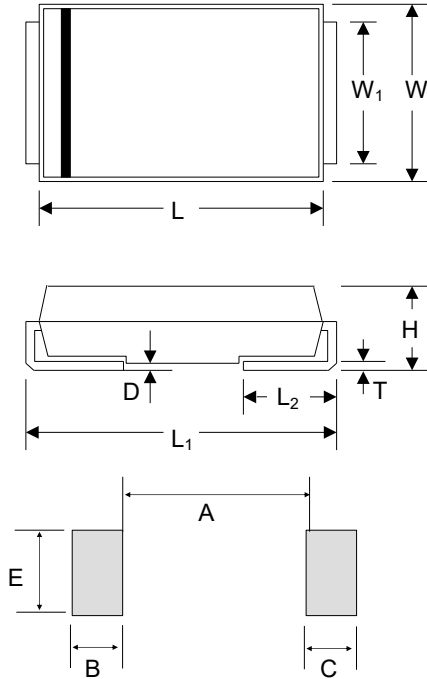
Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>PP</sub>	Repetitive peak pulse current	10 / 1000 μs	35	-	A
T <sub>J</sub>	Operating Temperature Range	-	-40	150	°C
T <sub>stg</sub>	Storage Temperature Range	-	-55	150	°C

Surge Rating	I <sub>PP</sub> (A) min				
	2 / 10 μs <sup>1</sup>	8 / 20 μs <sup>1</sup>	10 / 360 μs <sup>1</sup>	10 / 700 μs <sup>2</sup>	10 / 1000 μs <sup>1</sup>
A	100	90	50	50	35

Notes:

1. Current waveform in μs<sup>1</sup>.
2. Voltage waveform in μs<sup>2</sup>.

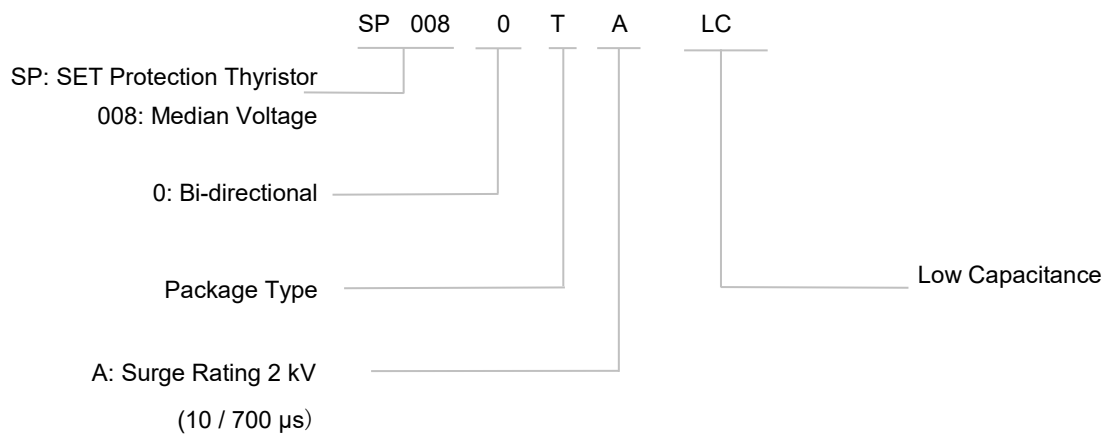
### Package Dimensions



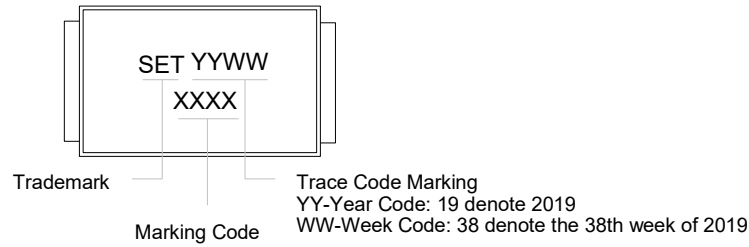
(Mounting Pad Layout)

Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
L	3.99	4.60	0.157	0.181
W	2.30	2.79	0.095	0.110
W <sub>1</sub>	1.25	1.65	0.049	0.065
H	1.90	2.29	0.075	0.090
T	0.152	0.305	0.006	0.012
L <sub>1</sub>	4.80	5.28	0.189	0.208
L <sub>2</sub>	0.78	1.52	0.030	0.060
D	-	0.203	-	0.008
A	-	2.30	-	0.090
B	2.10	-	0.082	-
C	2.10	-	0.082	-
E	1.80	-	0.070	-

### Part Numbering System



## Marking



## Electrical Characteristics

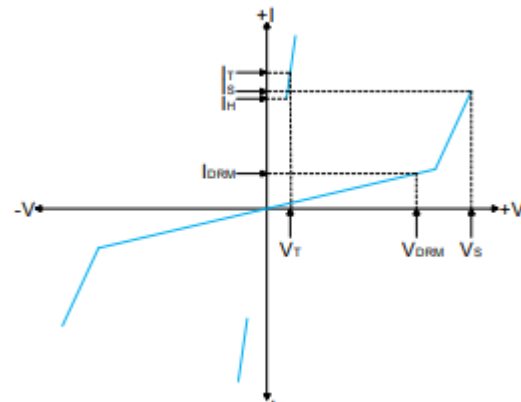
( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Part Number	Device Marking Code	$I_{DRM}@V_{DRM}$		$V_s\ ^1@I_s$		$V_T@I_T$		$I_H$	Capacitance <sup>2</sup>
		$\mu\text{A}$	V	V	mA	V	A	mA	pF
		Max		Max	Max	Max	Max	Min	Max
SP0080TALC	P8AC	1	6	15	800	4	2.2	10	10

Notes:

- $V_s$  is measured at 100 kV / S.
- Off-state capacitance is measured in VDC=2 V, VRMS=1 V, f=1 MHz.

Symbol	Parameter
$V_{DRM}$	Peak off-state voltage
$I_{DRM}$	Off-state current
$V_s$	Switching voltage
$I_s$	Switching current
$V_T$	On-state voltage
$I_T$	On-state current
$I_H$	Holding current
$C_o$	Off-state capacitance



### Performance Curve for Reference

(T<sub>A</sub>=25 °C unless otherwise noted)

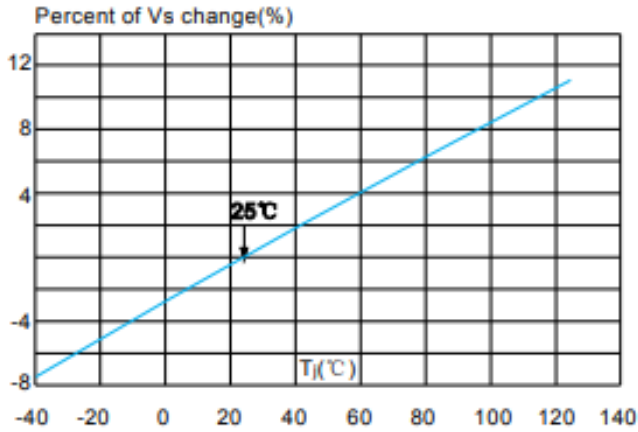


FIGURE 1  
Normalized VS. Change VS. Junction Temperature

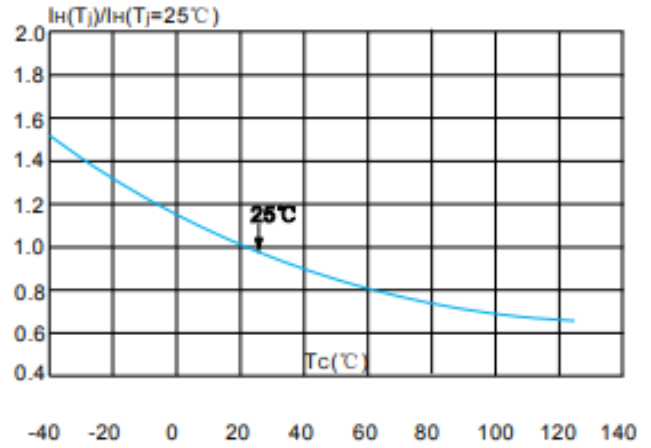


FIGURE 2  
Normalized DC Holding Current VS. Case Temperature

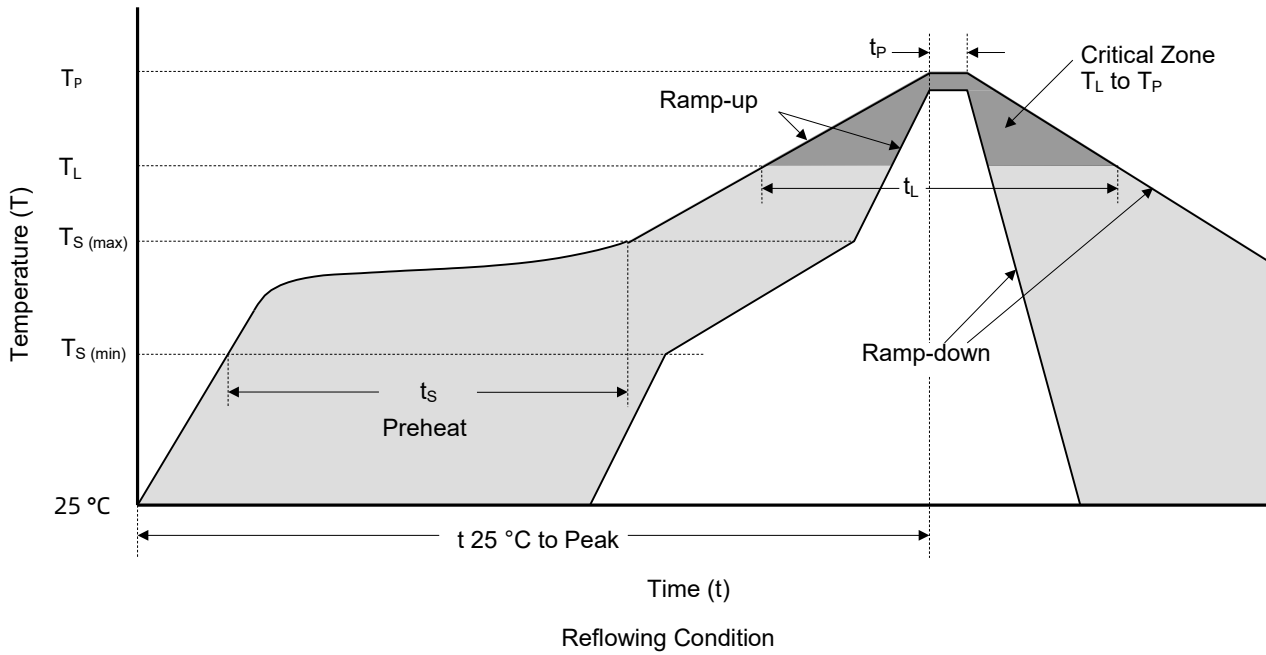
### Environmental Specifications

High Temp. Storage	JESD22-A103
HTRB	JESD22-A108
Temperature Cycling	JESD22-A104
MSL	JESDEC-J-STD-020, Level 1
H3TRB	JESD22-A101
RSH	JESD22-A111

### Physical Specifications

Weight	0.002ounce,0.061grams
Case	JESD22DO214AC. Molded plastic body over glass passivated junction
Polarity	Color band denotes positive end (cathode) except Bidirectional
Terminal	Matte Tin-plated leads, Solderability per JESD22-B102

### Soldering Parameters



Reflow Soldering Parameters		Lead-Free Assembly
Pre-heat	Temperature Min ( $T_{S(min)}$ )	150 °C
	Temperature Max ( $T_{S(max)}$ )	200 °C
	Time (min to max) ( $t_s$ )	60 ~ 120 seconds
Average Ramp Up Rate ( Liquidus Temp ( $T_L$ ) to Peak Temp ( $T_P$ ))		3 °C / second max.
$T_{S(max)}$ to $T_L$ -Ramp-up Rate		3 °C / second max.
Reflow	Temperature ( $T_L$ )	217 °C
	Time ( $t_L$ )	60 ~ 150 seconds
Peak Temperature ( $T_P$ )		260 <sup>+0/-5</sup> °C
Time of within 5 °C of Actual Peak Temperature ( $t_p$ )		30 seconds
Ramp-down Rate		6 °C / second max.
Time From 25 °C to Peak Temperature		8 Minutes max.
Do Not Exceed		260 °C

### Packaging Information

Tape	Symbol	Dimension (mm)
	W	12.00 ± 0.30 / -0.10
	P <sub>0</sub>	4.00 ± 0.10
	P <sub>1</sub>	8.00 ± 0.10
	P <sub>2</sub>	2.00 ± 0.05
	D <sub>0</sub>	1.55 ± 0.05
	D <sub>1</sub>	1.55 ± 0.05
	E	1.75 ± 0.10
	F	5.50 ± 0.05
	A <sub>0</sub>	2.79 ± 0.10
	B <sub>0</sub>	5.33 ± 0.10
	K <sub>0</sub>	2.36 ± 0.10
	T	0.30 ± 0.05

Reel Size	Symbol	Dimension (mm)
	A	330
	C	13.2
	W <sub>1</sub>	12.5

Part Number	Package	QTY's (Reel)	Packaging Option	Packaging Specification
SP0080TALC	DO-214AC	7500 PCS	Tape & Reel – 12 mm tape / 13" reel	EIA STD RS-481



# ATTENTION

## Usage

1. TSS must be operated in the specified ambient temp..
2. Do not clean the TSS with strong polar solvent such as ketone, esters, benzene and halogenated hydrocarbon, to avoid damaging the encapsulating layer.
3. Please do not apply severe vibration, shock or pressure to TSS, to avoid element cracking.

## Replacement

1. If TSS is visually damaged, please replace it.
2. TSS is a non-repairable product. For safety sake, please use equivalent TSS for replacement.

## Storage

1. Storage Temp. Range: (-55 to 150) °C.
2. Do not store the TSS at the high temp., high humidity or corrosive gas environment, to avoid influencing the solder- ability of the lead wires. The product shall be used up within 1 year after receiving the goods.

## Environmental Conditions

1. TSS should not be exposed to the open air, nor direct sunshine.
2. TSS should avoid rain, water vapor or other condition of high temp. and high humidity.
3. TSS should avoid sand dust, salt mist, or other harmful gases.

## Max. Typical Capacitance of TSS

The typical capacitance of TSS is listed in the specifications. Designers may refer to it when designing TSS in High frequency circuit.

## Installation Mechanical Stress

1. Do not knock TSS when installing, to avoid mechanical damage.
2. Please do not apply severe vibration, shock or pressure to TSS, to avoid surface resin or element cracking.

Thyristor Surge Suppressors (Surface Mount) Feature Overview

Package Type	Series								
DO-214AA	○	○	○	SPxxxxSB	SPxxxxSC	SPxxxxSD	○	○	○
DO-214AB	○	○	○	○	○	○	SPxxxxSDT	SP0080SDT-3L	○
DO-214AC	SP0080TALC	SP0080TBLC	SPxxxxSA	○	○	○	○	○	○
SOD-23-6	○	○	○	○	○	○	○	○	SIP5024G
Product Outline (mm)									
									
Surge Rating	A (2 kV @ 10/700 μs)	B (4 kV @ 10/700 μs)	B (4 kV @ 10/700 μs)	B (4 kV @ 10/700 μs)	C (6 kV @ 10/700 μs)	D (8 kV @ 10/700 μs)	DT (6 kV@ 1.2/50 μs)	DT (6 kV@ 1.2/50 μs)	NA
V <sub>DRM</sub> (V) Peak off-state voltage	6	6	58 ~ 340	6 ~ 400	6 ~ 440	6 ~ 400	6, 15, 400	6	24
I <sub>PP</sub> (A) (8/20 μs) Repetitive peak pulse current	90	250	250	250	400	700	3000	3000	35
C <sub>J</sub> (pF) capacitance	10	30	20 ~ 35	25 ~ 50	35 ~ 60	40 ~ 150	500, 250, 170	700	11
Operating Temperature (°C)	-55 to +150								